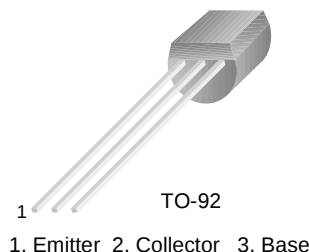


# 2N5306

2N5306

## NPN Darlington Transistor

- This device is designed for applications requiring extremely high current gain at currents to 1.0A.
- Sourced from process 05.
- See MPSA14 for characteristics.



## Absolute Maximum Ratings \* $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                                        | Value      | Units            |
|----------------|--------------------------------------------------|------------|------------------|
| $V_{CEO}$      | Collector-Emitter Voltage                        | 25         | V                |
| $V_{CBO}$      | Collector-Base Voltage                           | 25         | V                |
| $V_{EBO}$      | Emitter-Base Voltage                             | 12         | V                |
| $I_C$          | Collector Current - Continuous                   | 1.2        | A                |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range | -55 ~ +150 | $^\circ\text{C}$ |

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1. These ratings are based on a maximum junction temperature of 150 degrees C.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Electrical Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol                              | Parameter                             | Test Condition                                                                                                                          | Min.            | Typ. | Max.      | Units                          |
|-------------------------------------|---------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|-----------------|------|-----------|--------------------------------|
| <b>Off Characteristics</b>          |                                       |                                                                                                                                         |                 |      |           |                                |
| $V_{(BR)CEO}$                       | Collector-Emitter Breakdown Voltage * | $I_C = 10\text{mA}, I_B = 0$                                                                                                            | 25              |      |           | V                              |
| $V_{(BR)CBO}$                       | Collector-Base Breakdown Voltage      | $I_C = 0.1\mu\text{A}, I_E = 0$                                                                                                         | 25              |      |           | V                              |
| $V_{(BR)EBO}$                       | Emitter-Base Breakdown Voltage        | $I_E = 0.1\mu\text{A}, I_C = 0$                                                                                                         | 12              |      |           | V                              |
| $I_{CBO}$                           | Collector Cutoff Current              | $V_{CB} = 25\text{V}, I_E = 0$<br>$V_{CB} = 25\text{V}, I_E = 0, T_a = 100^\circ\text{C}$                                               |                 |      | 0.1<br>20 | $\mu\text{A}$<br>$\mu\text{A}$ |
| $I_{EBO}$                           | Emitter Cutoff Current                | $V_{EB} = 12\text{V}, I_C = 0$                                                                                                          |                 |      | 0.1       | $\mu\text{A}$                  |
| <b>On Characteristics *</b>         |                                       |                                                                                                                                         |                 |      |           |                                |
| $h_{FE}$                            | DC Current Gain                       | $V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$<br>$V_{CE} = 5.0\text{V}, I_C = 100\text{mA}$                                                | 7,000<br>20,000 |      | 70,000    |                                |
| $V_{CE(sat)}$                       | Collector-Emitter Saturation Voltage  | $I_C = 200\text{mA}, I_B = 0.2\text{mA}$                                                                                                |                 |      | 1.4       | V                              |
| $V_{BE(sat)}$                       | Base-Emitter Saturation Voltage       | $I_C = 200\text{mA}, I_B = 0.2\text{mA}$                                                                                                |                 |      | 1.6       | V                              |
| $V_{BE(on)}$                        | Base-Emitter On Voltage               | $I_C = 200\text{mA}, V_{CE} = 5.0\text{V}$                                                                                              |                 |      | 1.5       | V                              |
| <b>Small Signal Characteristics</b> |                                       |                                                                                                                                         |                 |      |           |                                |
| $C_{cb}$                            | Collector-Base Capacitance            | $V_{CB} = 10\text{V}, f = 1.0\text{MHz}$                                                                                                |                 |      | 10        | pF                             |
| $h_{fe}$                            | Small-Signal Current Gain             | $I_C = 2.0\text{mA}, V_{CE} = 5.0\text{V},$<br>$f = 1.0\text{KHz}$<br>$I_C = 2.0\text{mA}, V_{CE} = 5.0\text{V},$<br>$f = 10\text{MHz}$ | 7000<br>6.0     |      |           |                                |

\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**Thermal Characteristics**  $T_A=25^{\circ}\text{C}$  unless otherwise noted

| Symbol          | Parameter                                                     | Max.       | Units                        |
|-----------------|---------------------------------------------------------------|------------|------------------------------|
| $P_D$           | Total Device Dissipation<br>Derate above $25^{\circ}\text{C}$ | 625<br>5.0 | mW<br>mW/ $^{\circ}\text{C}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case                          | 83.3       | $^{\circ}\text{C/W}$         |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient                       | 200        | $^{\circ}\text{C/W}$         |

# Package Dimensions

## TO-92



Dimensions in Millimeters

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